EconoPIM™2 module with TRENCHSTOP™IGBT7 and emitter controlled 7 diode and PressFIT / NTC / TIM

Features

- Electrical features
  - V_{CES} = 1200 V
  - $I_{C\ nom}$ = 75 A / I_{CRM} = 150 A
  - TRENCHSTOP™ IGBT7
  - Low $V_{CE,sat}$
  - Overload operation up to 175°C
- Mechanical features
  - High power and thermal cycling capability
  - Integrated NTC temperature sensor
  - Copper base plate
  - Al_2O_3 substrate with low thermal resistance
  - PressFIT contact technology
  - Pre-applied thermal interface material

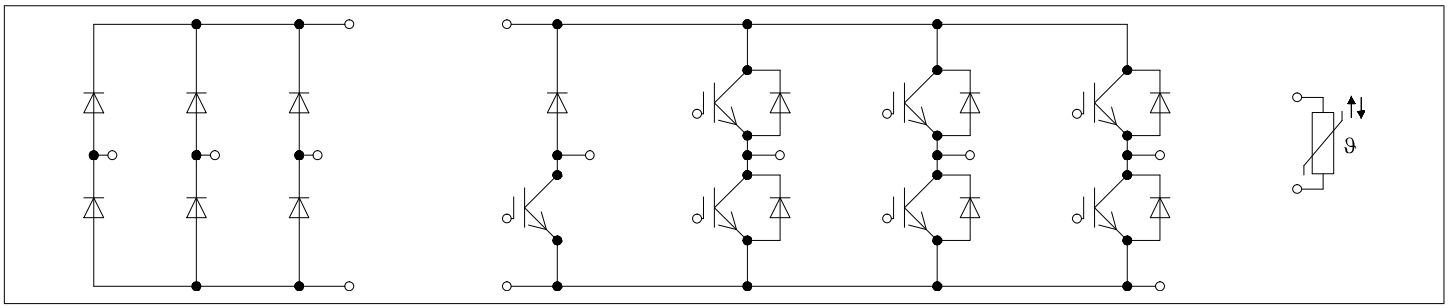
Potential applications

- Auxiliary inverters
- Motor drives
- Servo drives

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description



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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f = 50 Hz, *t* = 1 min	2.5	kV
Material of module baseplate			Cu	
Internal Isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to heatsink	7.5	mm
Comparative tracking index	*CTI*		> 200	
RTI Elec.	*RTI*	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray inductance module	L_{sCE}				35		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	T_H=25°C, per switch			5.6		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	T_H=25°C, per switch			5.3		mΩ
Storage temperature	T_{stg}			-40		125	°C
Maximum baseplate operation temperature	T_{BPmax}					125	°C
Mounting torque for modul mounting	*M*	- Mounting according to valid application note	M5, Screw	3		6	Nm
Weight	*G*				180		g

Note: The current under continuous operation is limited to 50 A rms per connector pin.
Storage and shipment of modules with TIM => see AN2012-07

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V
Continous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_H = 75 °C	75	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		150	A

(table continues...)

Table 3 **(continued) Maximum rated values**

Parameter	Symbol	Note or test condition	Values	Unit
Gate-emitter peak voltage	V_{GES}		±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	I_C = 75 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.55	1.80	V
			T_{vj} = 125 °C		1.69		
			T_{vj} = 175 °C		1.77		
Gate threshold voltage	V_{GEth}	I_C = 1.28 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 600 V			1.25		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			2		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			15.1		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.053		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.014	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 75 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 5.6 Ω	T_{vj} = 25 °C		0.146		µs
			T_{vj} = 125 °C		0.162		
			T_{vj} = 175 °C		0.169		
Rise time (inductive load)	t_r	I_C = 75 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 5.6 Ω	T_{vj} = 25 °C		0.053		µs
			T_{vj} = 125 °C		0.057		
			T_{vj} = 175 °C		0.060		
Turn-off delay time (inductive load)	t_{doff}	I_C = 75 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 5.6 Ω	T_{vj} = 25 °C		0.320		µs
			T_{vj} = 125 °C		0.390		
			T_{vj} = 175 °C		0.440		
Fall time (inductive load)	t_f	I_C = 75 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 5.6 Ω	T_{vj} = 25 °C		0.110		µs
			T_{vj} = 125 °C		0.200		
			T_{vj} = 175 °C		0.270		
Turn-on energy loss per pulse	E_{on}	I_C = 75 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 5.6 Ω, di/dt = 1050 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		8.05		mJ
			T_{vj} = 125 °C		10.6		
			T_{vj} = 175 °C		12.3		
Turn-off energy loss per pulse	E_{off}	I_C = 75 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 5.6 Ω, dv/dt = 3150 V/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		4.95		mJ
			T_{vj} = 125 °C		7.76		
			T_{vj} = 175 °C		9.51		

(table continues...)

Table 4 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} \leq$ 15 V, V_{CC} = 800 V, $V_{CEmax}=V_{CES}-L_{sCE}*di/dt$	$t_P \leq$ 8 µs, T_{vj} = 150 °C		260		A
			$t_P \leq$ 7 µs, T_{vj} = 175 °C		250		
Thermal resistance, junction to heatsink	R_{thJH}	per IGBT, Valid with IFX pre-applied Thermal Interface Material				0.663	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: *Tvj op > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN2018-14.*

3 Diode, Inverter

Table 5 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continous DC forward current	I_F			75	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		150	A
I^2t - value	I^2t	V_R = 0 V, t_P = 10 ms	T_{vj} = 125 °C	1150	A^2s
			T_{vj} = 175 °C	740	

Table 6 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 75 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.72	2.10	V
			T_{vj} = 125 °C		1.59		
			T_{vj} = 175 °C		1.52		
Peak reverse recovery current	I_{RM}	I_F = 75 A, V_R = 600 V, V_{GE} = -15 V, $-di_F/dt$ = 1050 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		38		A
			T_{vj} = 125 °C		51		
			T_{vj} = 175 °C		59		

(table continues...)

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Recovered charge	Q_r	I_F = 75 A, V_R = 600 V, V_{GE} = -15 V, -di$_F$/dt = 1050 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		5.43		µC
			T_{vj} = 125 °C		10.4		
			T_{vj} = 175 °C		14.1		
Reverse recovery energy	E_{rec}	I_F = 75 A, V_R = 600 V, V_{GE} = -15 V, -di$_F$/dt = 1050 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		1.79		mJ
			T_{vj} = 125 °C		3.5		
			T_{vj} = 175 °C		4.83		
Thermal resistance, junction to heatsink	R_{thJH}	per diode, Valid with IFX pre-applied Thermal Interface Material				0.917	K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		175	°C

Note: Tvj op > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN2018-14.

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} = 150 °C		1600	V
Maximum RMS forward current per chip	I_{FRMSM}	T_H = 80 °C		75	A
Maximum RMS current at rectifier output	I_{RMSM}	T_H = 80 °C		100	A
Surge forward current	I_{FSM}	t_P = 10 ms	T_{vj} = 25 °C	745	A
			T_{vj} = 150 °C	515	
I^2t - value	I^2t	t_P = 10 ms	T_{vj} = 25 °C	2780	A^2s
			T_{vj} = 150 °C	1330	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 75 A	T_{vj} = 150 °C		1.06		V
Reverse current	I_r	T_{vj} = 150 °C, V_R = 1600 V			1		mA
Thermal resistance, junction to heatsink	R_{thJH}	per diode, Valid with IFX pre-applied Thermal Interface Material				0.905	K/W

Table 8 **(continued) Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj, op}$		-40		150	°C

5 IGBT, Brake-Chopper

Table 9 **Maximum rated values**

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		T_{vj} = 25 °C	1200	V
Continous DC collector current	I_{CDC}	$T_{vj\,max}$ = 175 °C	T_H = 95 °C	50	A
Repetitive peak collector current	I_{CRM}	t_P = 1 ms		100	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\,sat}$	I_C = 50 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.50	1.80	V
			T_{vj} = 125 °C		1.64		
			T_{vj} = 175 °C		1.72		
Gate threshold voltage	V_{GEth}	I_C = 1.28 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		5.15	5.80	6.45	V
Gate charge	Q_G	V_{GE} = ±15 V, V_{CE} = 600 V			0.92		µC
Internal gate resistor	R_{Gint}	T_{vj} = 25 °C			0		Ω
Input capacitance	C_{ies}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			11.1		nF
Reverse transfer capacitance	C_{res}	f = 100 kHz, T_{vj} = 25 °C, V_{CE} = 25 V, V_{GE} = 0 V			0.039		nF
Collector-emitter cut-off current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			0.007	mA
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25 °C				100	nA
Turn-on delay time (inductive load)	t_{don}	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω	T_{vj} = 25 °C		0.059		µs
			T_{vj} = 125 °C		0.061		
			T_{vj} = 175 °C		0.062		
Rise time (inductive load)	t_r	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω	T_{vj} = 25 °C		0.035		µs
			T_{vj} = 125 °C		0.039		
			T_{vj} = 175 °C		0.041		

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off delay time (inductive load)	t_{doff}	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω	T_{vj} = 25 °C		0.290		µs
			T_{vj} = 125 °C		0.380		
			T_{vj} = 175 °C		0.420		
Fall time (inductive load)	t_f	I_C = 50 A, V_{CE} = 600 V, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω	T_{vj} = 25 °C		0.110		µs
			T_{vj} = 125 °C		0.200		
			T_{vj} = 175 °C		0.270		
Turn-on energy loss per pulse	E_{on}	I_C = 50 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Gon} = 7.5 Ω, di/dt = 1145 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		3.37		mJ
			T_{vj} = 125 °C		4.26		
			T_{vj} = 175 °C		4.66		
Turn-off energy loss per pulse	E_{off}	I_C = 50 A, V_{CE} = 600 V, L_σ = 35 nH, V_{GE} = ±15 V, R_{Goff} = 7.5 Ω, dv/dt = 2940 V/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		3.33		mJ
			T_{vj} = 125 °C		5.32		
			T_{vj} = 175 °C		6.58		
SC data	I_{SC}	$V_{GE} \leq$ 15 V, V_{CC} = 800 V, V_{CEmax}=V_{CES}-L_{sCE}*di/dt	$t_P \leq$ 8 µs, T_{vj} = 150 °C		190		A
			$t_P \leq$ 7 µs, T_{vj} = 175 °C		180		
Thermal resistance, junction to heatsink	R_{thJH}	per IGBT, Valid with IFX pre-applied Thermal Interface Material				0.777	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: Tvj op > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN2018-14.

6 Diode, Brake-Chopper

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		T_{vj} = 25 °C	1200	V
Continous DC forward current	I_F			25	A
Repetitive peak forward current	I_{FRM}	t_P = 1 ms		50	A
I^2t - value	I^2t	V_R = 0 V, t_P = 10 ms	T_{vj} = 150 °C	125	A^2s
			T_{vj} = 175 °C	95	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	I_F = 25 A, V_{GE} = 0 V	T_{vj} = 25 °C		1.83	2.10	V
			T_{vj} = 125 °C		1.70		
			T_{vj} = 175 °C		1.63		
Peak reverse recovery current	I_{RM}	I_F = 25 A, V_R = 600 V, V_{GE} = -15 V, -di$_F$/dt = 375 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		19.2		A
			T_{vj} = 125 °C		19.3		
			T_{vj} = 175 °C		19.4		
Recovered charge	Q_r	I_F = 25 A, V_R = 600 V, V_{GE} = -15 V, -di$_F$/dt = 375 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		1.59		µC
			T_{vj} = 125 °C		1.63		
			T_{vj} = 175 °C		1.64		
Reverse recovery energy	E_{rec}	I_F = 25 A, V_R = 600 V, V_{GE} = -15 V, -di$_F$/dt = 375 A/µs (T_{vj} = 175 °C)	T_{vj} = 25 °C		0.64		mJ
			T_{vj} = 125 °C		0.66		
			T_{vj} = 175 °C		0.67		
Thermal resistance, junction to heatsink	R_{thJH}	per diode, Valid with IFX pre-applied Thermal Interface Material				1.63	K/W
Temperature under switching conditions	$T_{vj\,op}$			-40		175	°C

Note: Tvj op > 150°C is allowed for operation at overload conditions. For detailed specifications, please refer to AN2018-14.

7 NTC-Thermistor

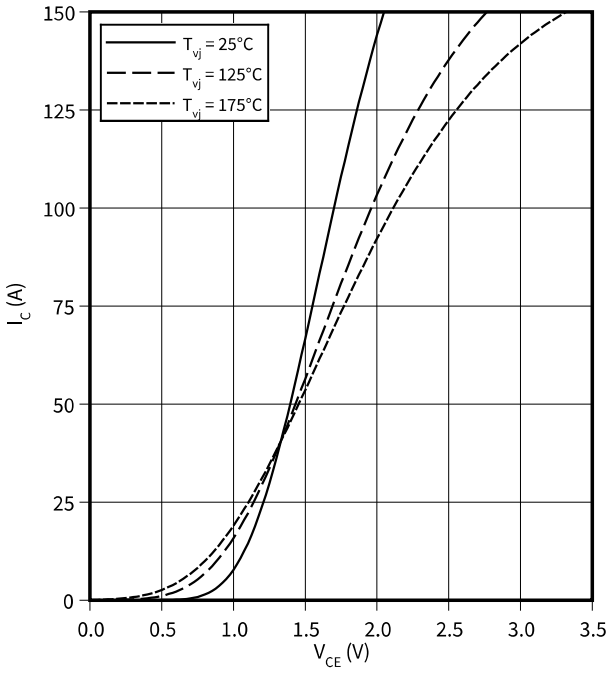
Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	T_{NTC} = 25 °C		5		kΩ
Deviation of R_{100}	$\Delta R/R$	T_{NTC} = 100 °C, R_{100} = 493 Ω	-5		5	%
Power dissipation	P_{25}	T_{NTC} = 25 °C			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2\text{-}1/(298{,}15\ K))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2\text{-}1/(298{,}15\ K))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2\text{-}1/(298{,}15\ K))]$		3433		K

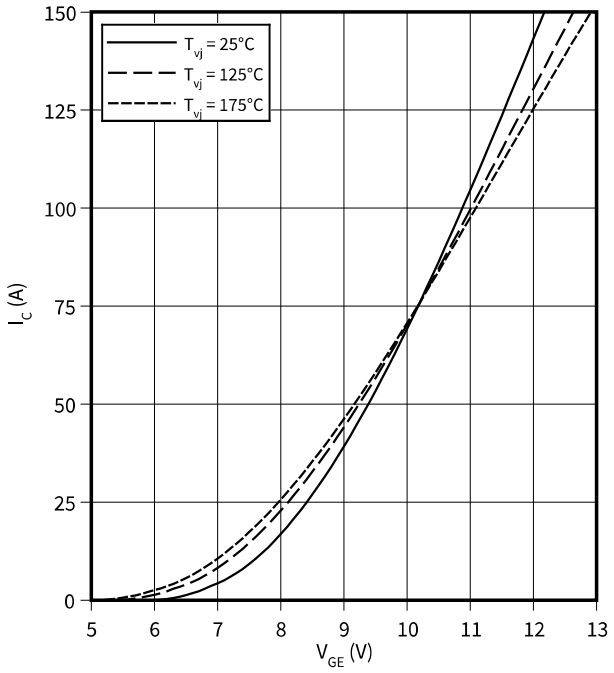
Note: Specification according to the valid application note.

8 Characteristics diagrams

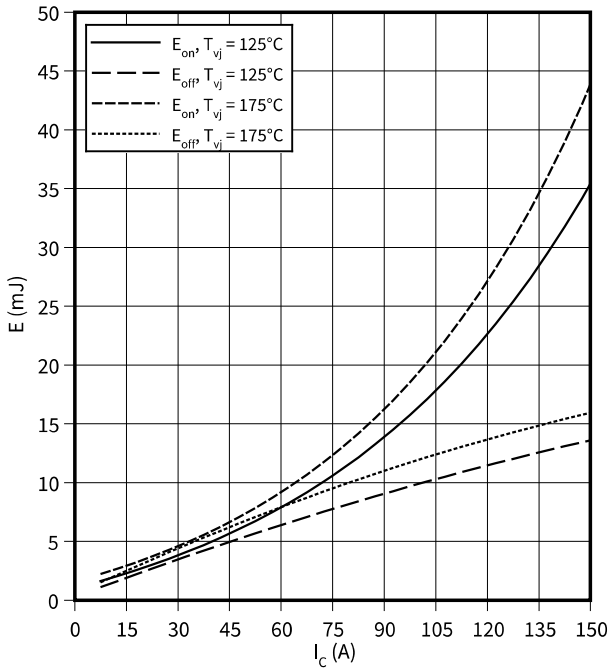
output characteristic (typical), IGBT, Inverter
$I_C = f(V_{CE})$
V_{GE} = 15 V



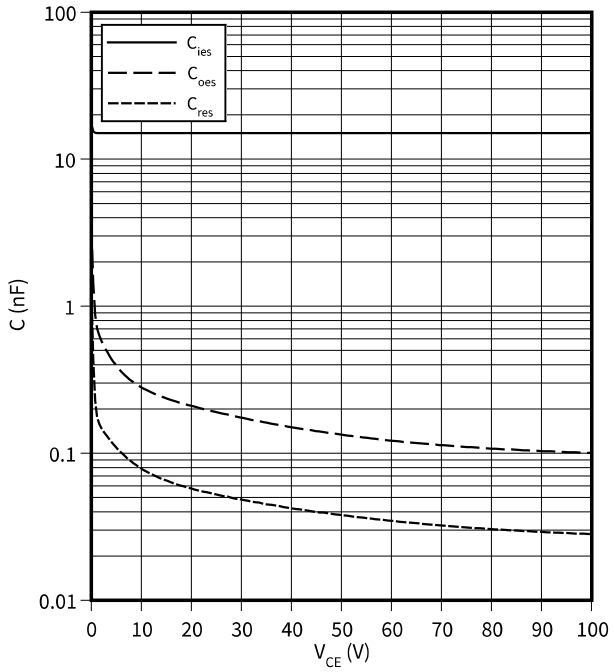
transfer characteristic (typical), IGBT, Inverter
$I_C = f(V_{GE})$
V_{CE} = 20 V



switching losses (typical), IGBT, Inverter
$E = f(I_C)$
V_{CE} = 600 V, V_{GE} = ± 15 V, R_{Goff} = 5.6 Ω, R_{Gon} = 5.6 Ω



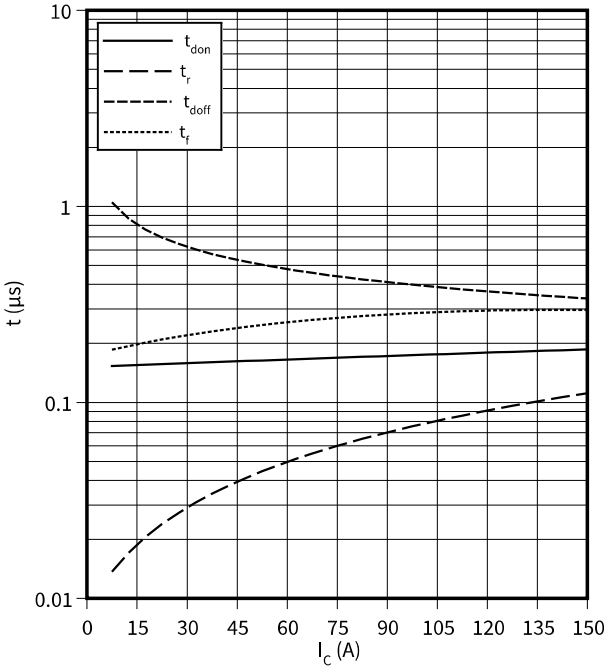
capacity characteristic (typical), IGBT, Inverter
$C = f(V_{CE})$
f = 100 kHz, V_{GE} = 0 V, T_{vj} = 25 °C



switching times (typical), IGBT, Inverter

$t = f(I_C)$

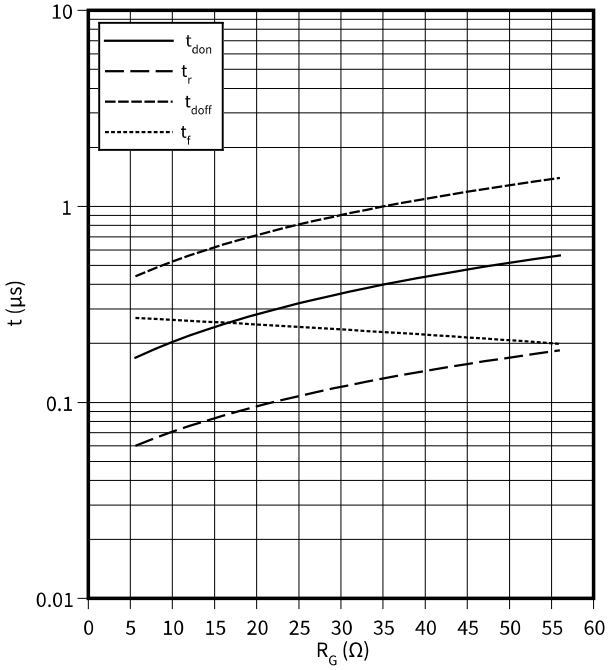
$R_{Goff} = 5.6\ \Omega$, $R_{Gon} = 5.6\ \Omega$, $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V, $T_{vj} = 175$ °C



switching times (typical), IGBT, Inverter

$t = f(R_G)$

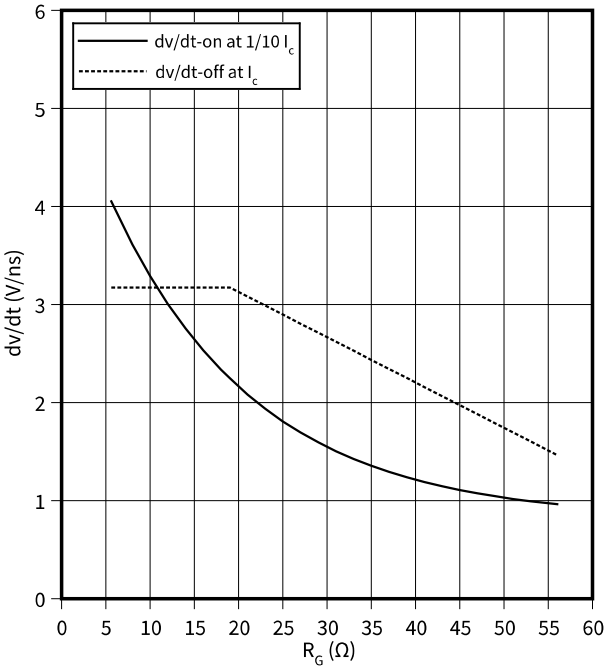
$I_C = 75$ A, $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V, $T_{vj} = 175$ °C



dv/dt (typical), IGBT, Inverter

$dv/dt = f(R_G)$

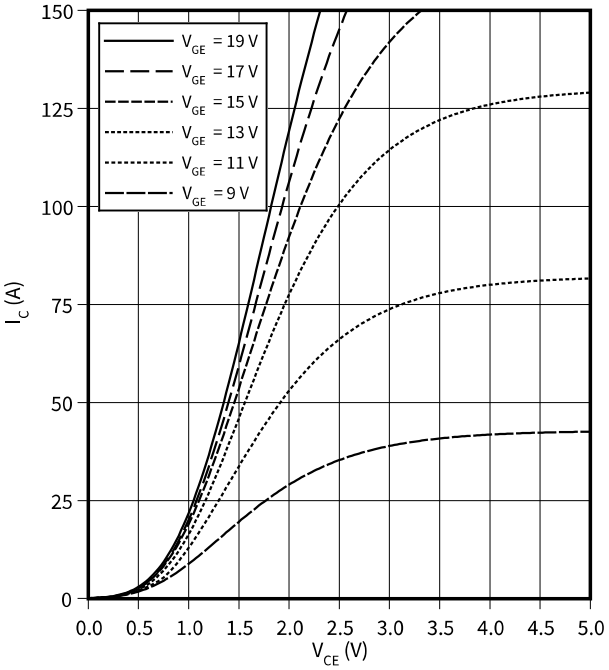
$I_C = 75$ A, $V_{CE} = 600$ V, $V_{GE} = \pm 15$ V, $T_{vj} = 25$ °C



output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

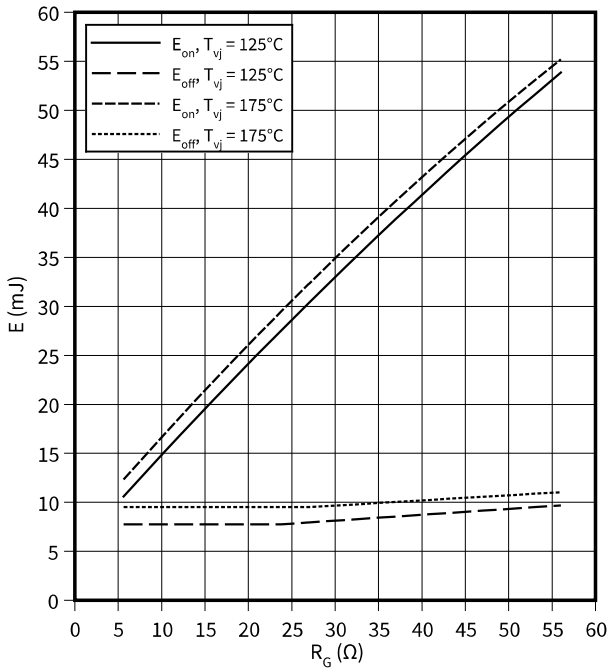
$T_{vj} = 175$ °C



switching losses (typical), IGBT, Inverter

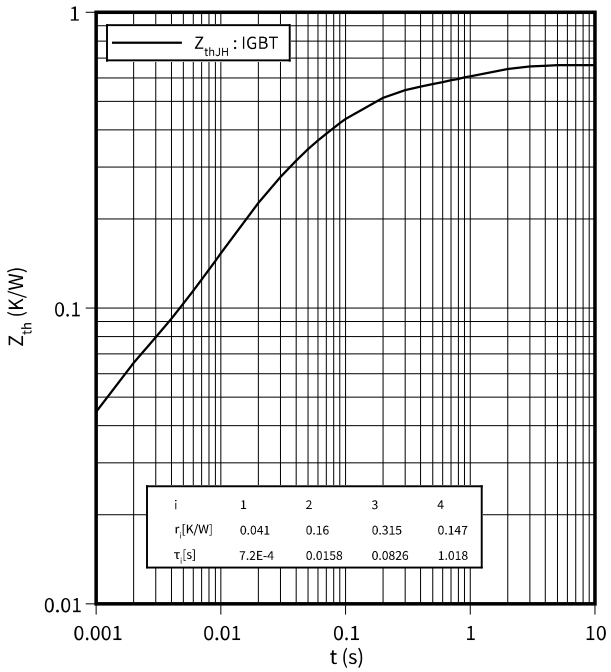
$E = f(R_G)$

$I_C = 75\ A, V_{CE} = 600\ V, V_{GE} = \pm 15\ V$



transient thermal impedance , IGBT, Inverter

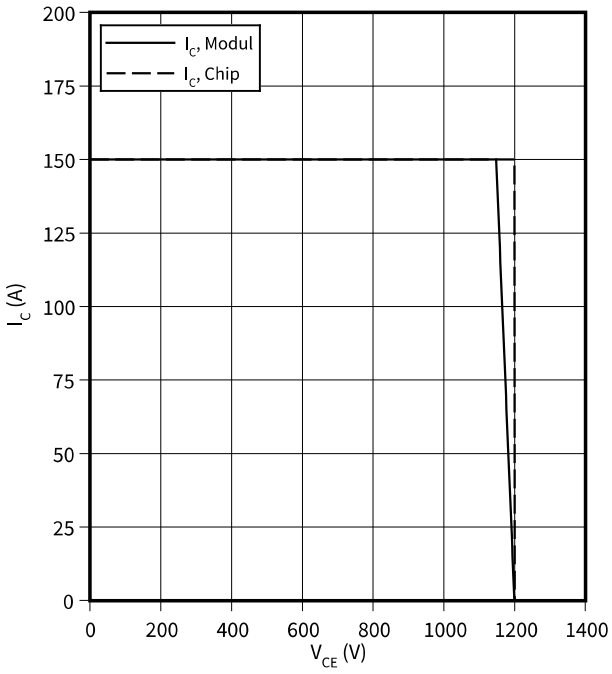
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

$I_C = f(V_{CE})$

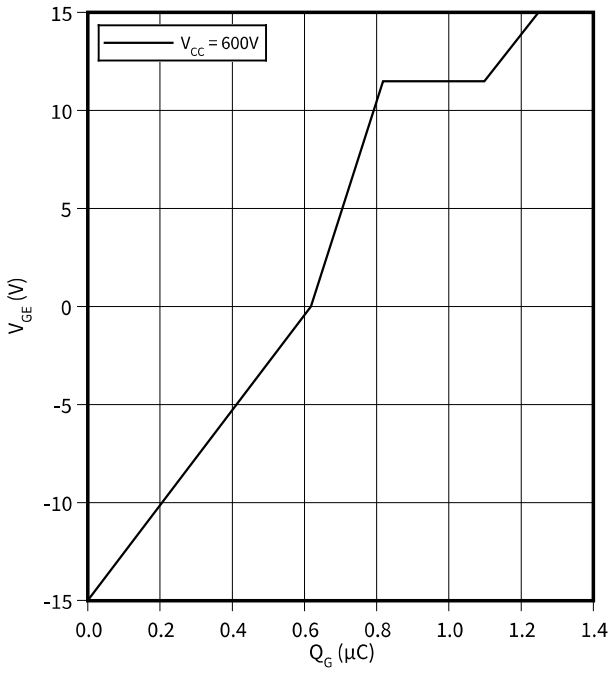
$V_{GE} = \pm 15\ V, T_{vj} = 175\ °C, R_{Goff} = 5.6\ \Omega$



gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$

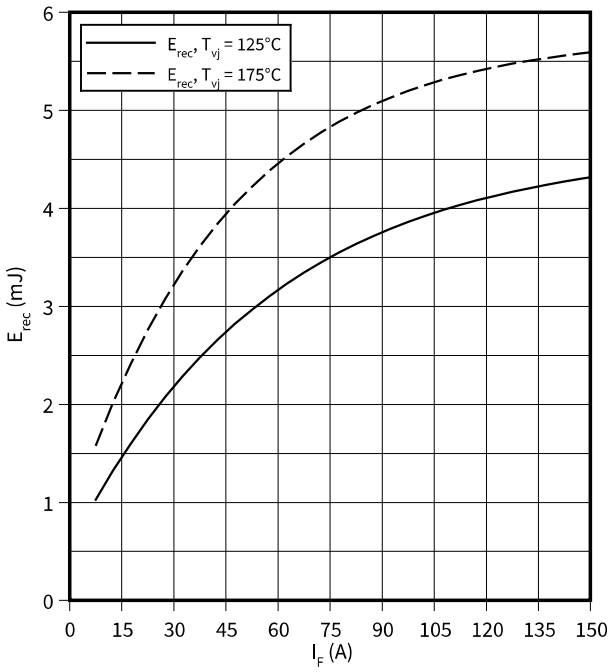
$I_C = 75\ A, T_{vj} = 25\ °C$



switching losses (typical), Diode, Inverter

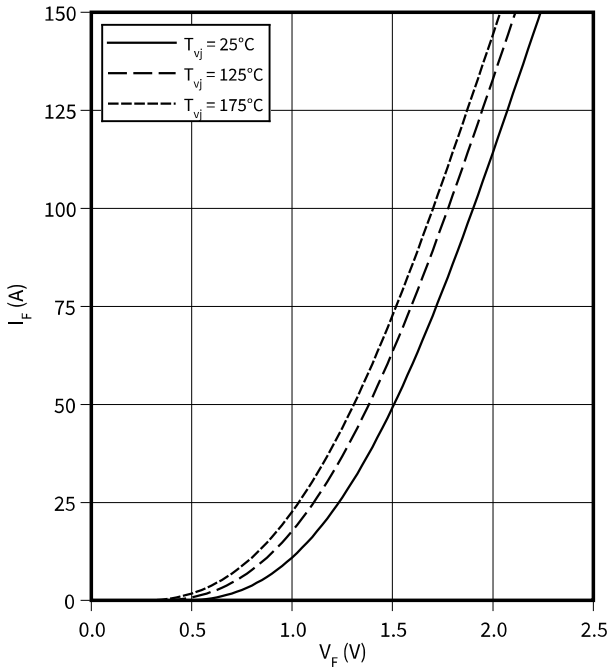
$E_{rec} = f(I_F)$

$R_{Gon} = 5.6\ \Omega$, $V_{CE} = 600\ V$



forward characteristic (typical), Diode, Inverter

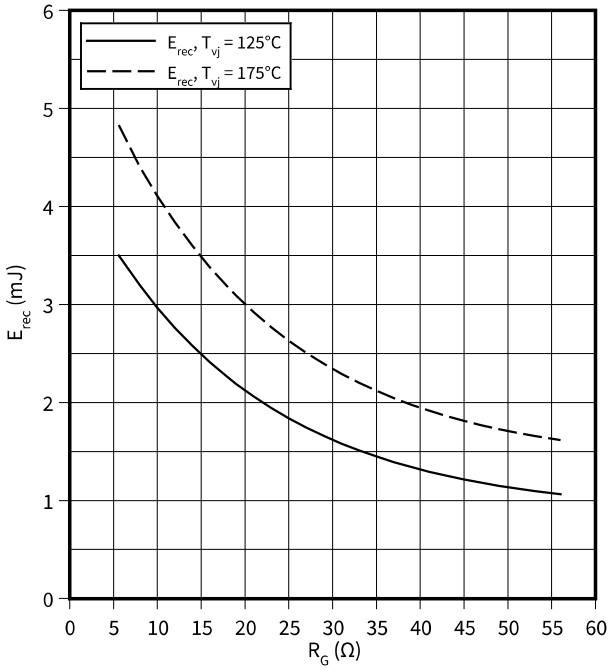
$I_F = f(V_F)$



switching losses (typical), Diode, Inverter

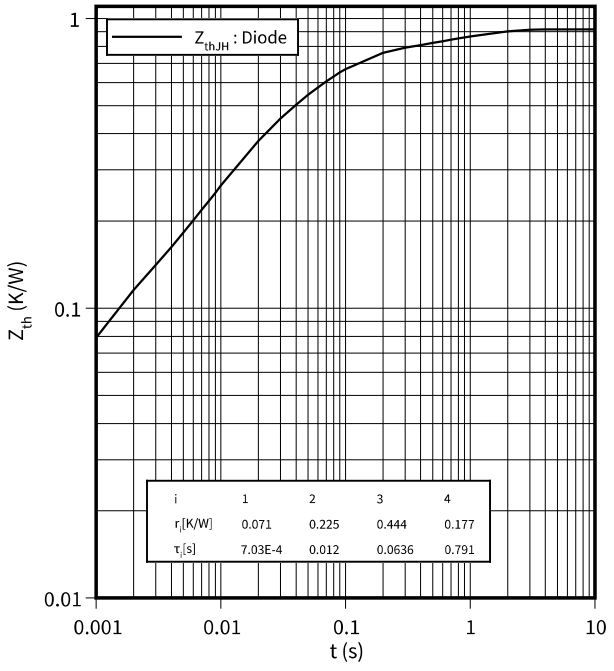
$E_{rec} = f(R_G)$

$V_{CE} = 600\ V$, $I_F = 75\ A$



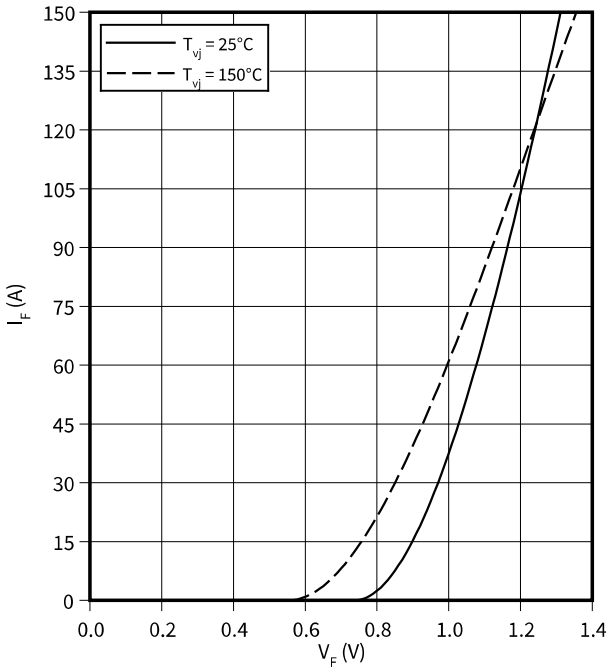
transient thermal impedance , Diode, Inverter

$Z_{th} = f(t)$



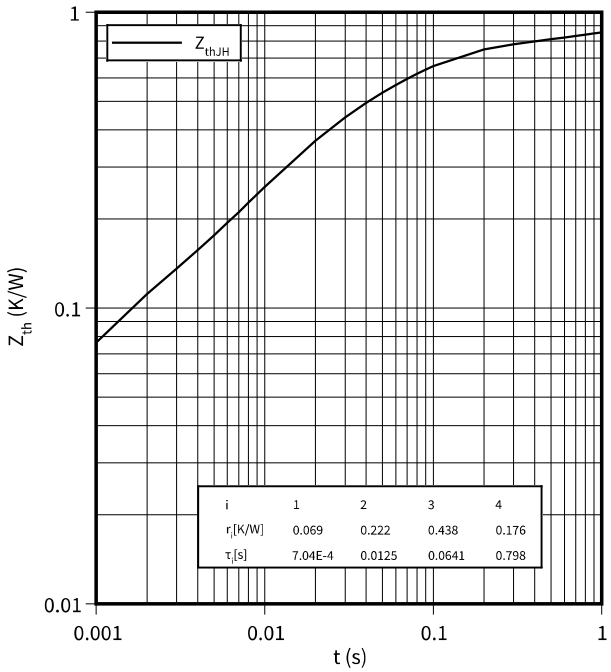
Forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



Transient thermal impedance, Diode, Rectifier

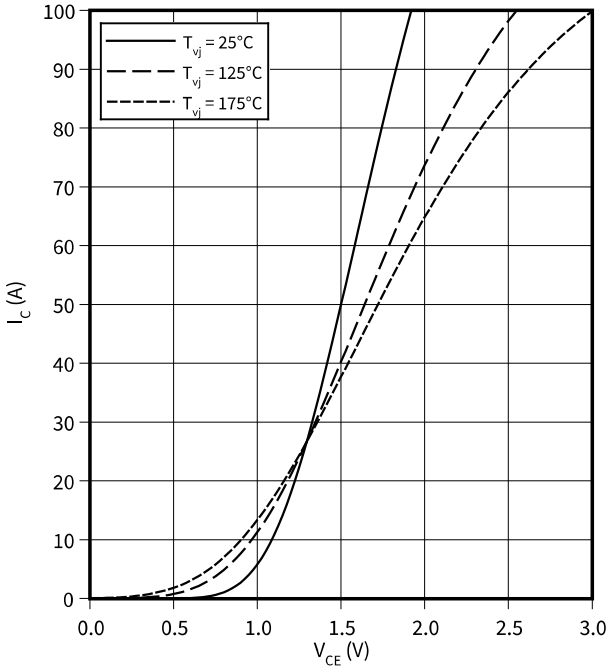
$Z_{th} = f(t)$



output characteristic (typical), IGBT, Brake-Chopper

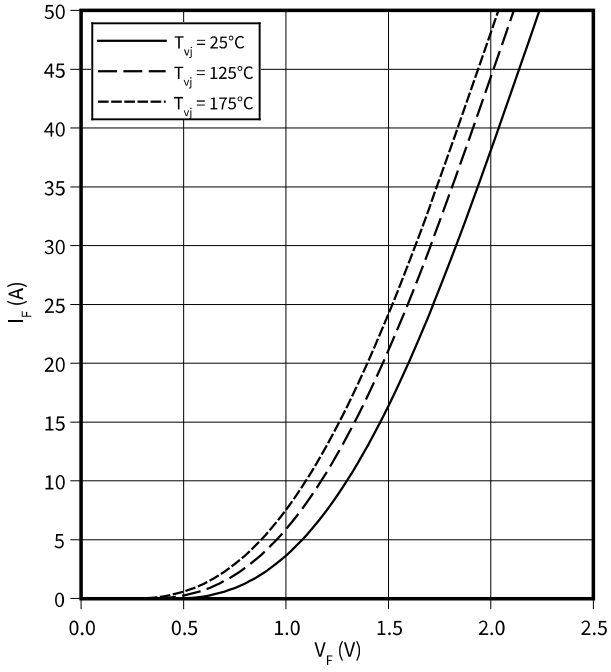
$I_C = f(V_{CE})$

$V_{GE} = 15$ V



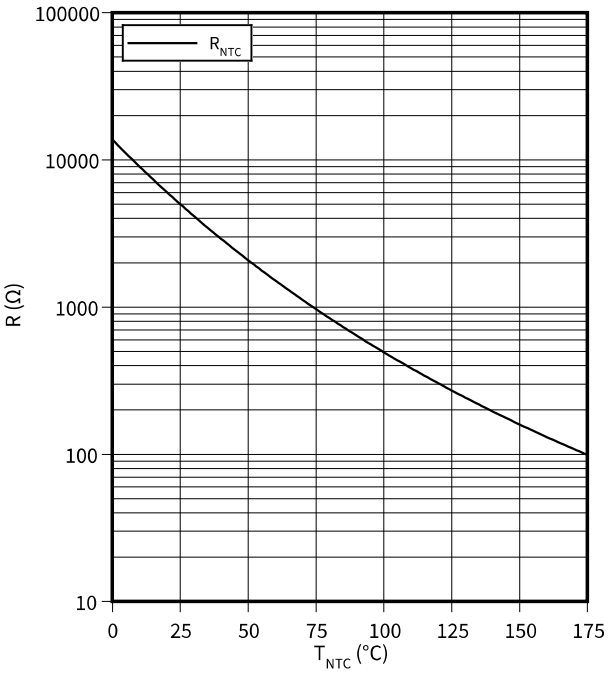
forward characteristic (typical), Diode, Brake-Chopper

$I_F = f(V_F)$



temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



9 Circuit diagram

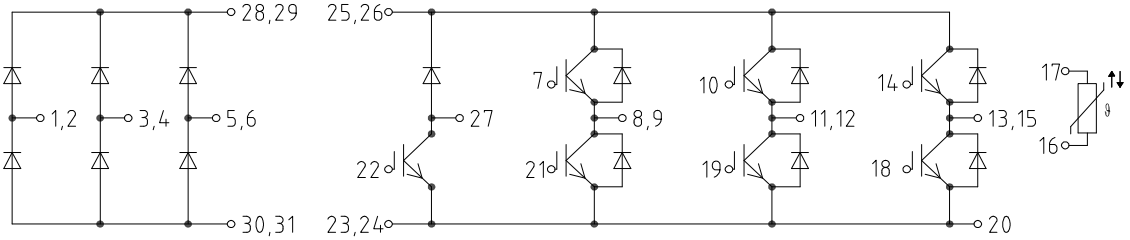


Figure 1

10 Package outlines

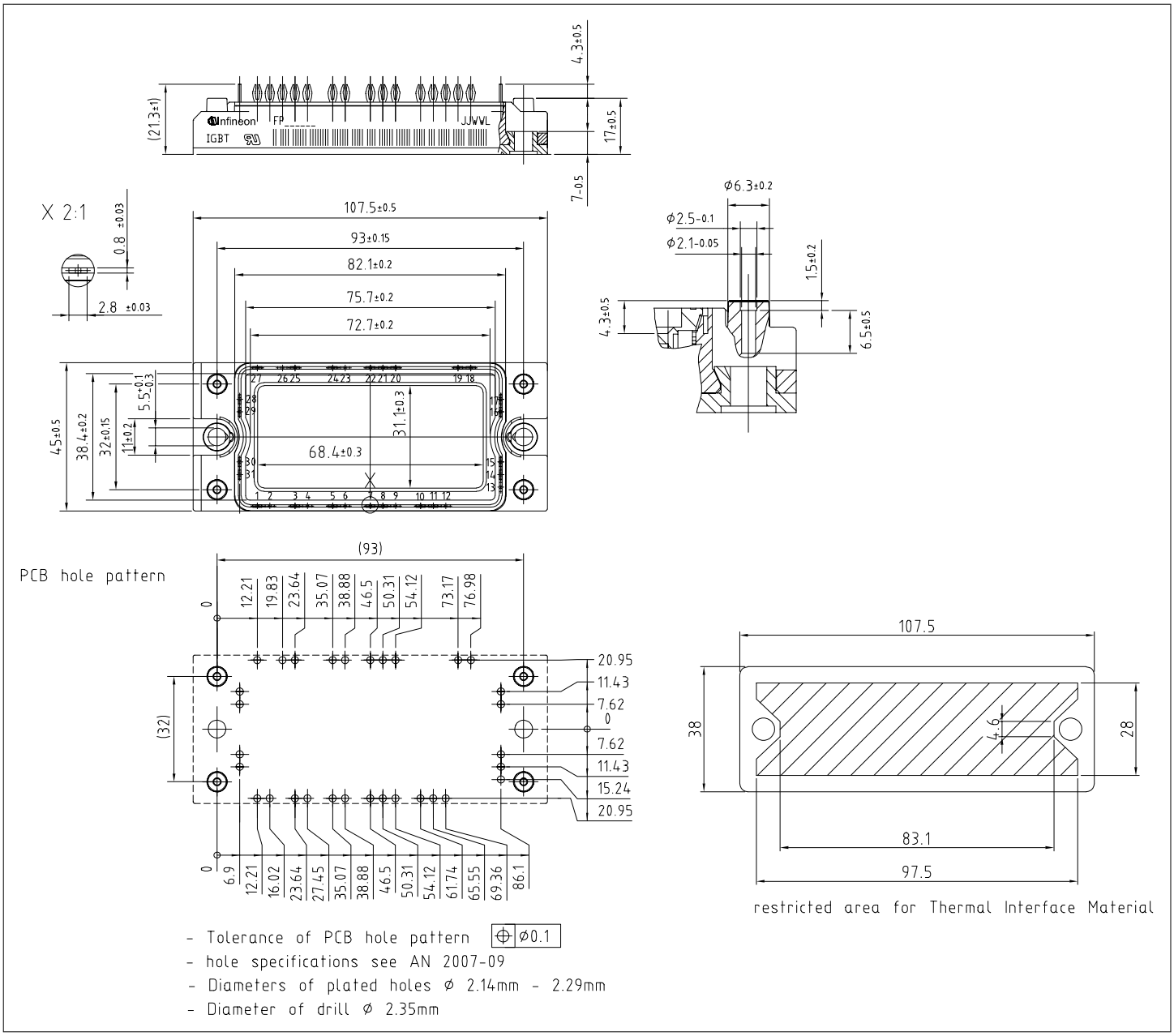


Figure 2

11 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	*Content* Module serial number Module material number Production order number Date code (production year) Date code (production week)	*Digit* 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	*Example* 71549 142846 55054991 15 30
Example	 7154914284655054991530		 7154914284655054991530

Figure 3

Revision history

Document revision	Date of release	Description of changes
1.00	2021-09-28	Initial version

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